Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- Very low Drain-Source on-state resistance R_{DSon} = 42 m Ω in high density
- 1 kV ESD protected

3. Applications

- Low-side load switch and charging switch for portable devices
- Power management in battery-driven portables
- LED driver
- DC-to-DC converters

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	3.2	Α
Static characte	eristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3.2 \text{ A}; T_j = 25 \text{ °C}$		-	42	54	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D I
2	S	source	<u> </u>	
3	D	drain	4 3	G $+$ $+$ $+$ $+$
4	D	drain	2	
			Transparent top view DFN1010D-3 (SOT1215)	S 017aaa255

6. Ordering information

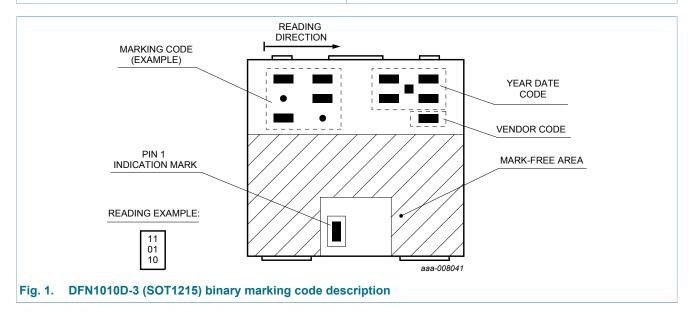
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMXB43UNE	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB43UNE	11 00 00



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20 V, N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	3.2	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	2.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	12.8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	0.4	W
			[1]	-	1.07	W
		T _{sp} = 25 °C		-	8.33	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	diode					
Is	source current	T _{amb} = 25 °C	[1]	-	0.9	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

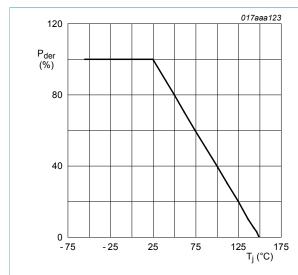


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

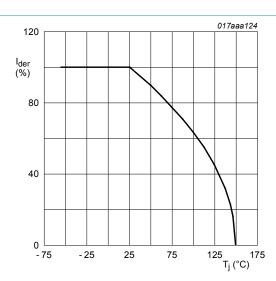


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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20 V, N-channel Trench MOSFET

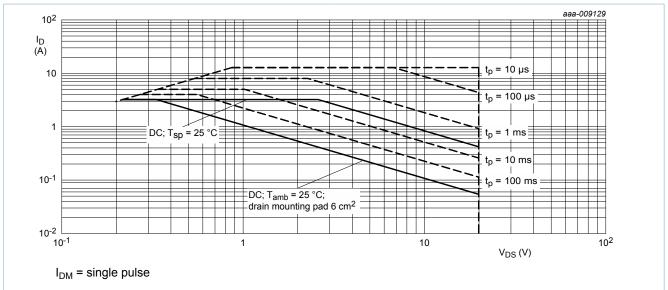


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	271	311	K/W
			[2]	-	102	117	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

20 V, N-channel Trench MOSFET

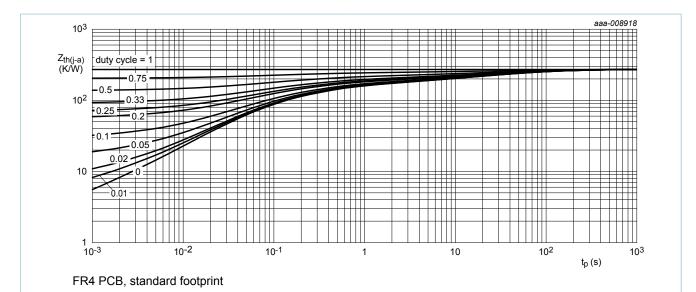
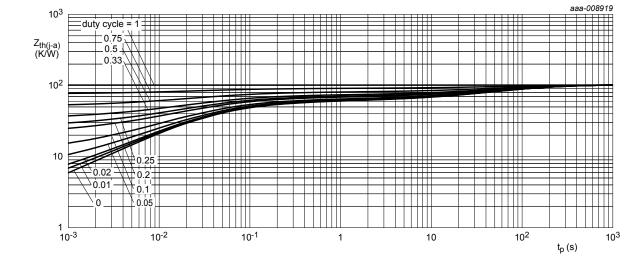


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain $6\ \mathrm{cm}^2$

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μA
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	1	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I_D = 3.2 A; T_j = 25 °C	-	42	54	mΩ
resistance	resistance	V_{GS} = 4.5 V; I_D = 3.2 A; T_j = 150 °C	-	64	83	mΩ
		V_{GS} = 2.5 V; I_D = 3.1 A; T_j = 25 °C	-	48	68	mΩ
		V _{GS} = 1.8 V; I _D = 1 A; T _j = 25 °C	-	56	90	mΩ
	V_{GS} = 1.5 V; I_D = 0.1 A; T_j = 25 °C	-	64	120	mΩ	
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 3.2 A; T_{j} = 25 °C	-	28	-	S
R_G	gate resistance	f = 1 MHz; T _{j=} = 25 °C	-	0.84	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 10 \text{ V}; I_D = 3.2 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	5.7	10	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.6	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	551	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	57	-	pF
C _{rss}	reverse transfer capacitance		-	46	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 10 \text{ V}; I_D = 3.2 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	20	-	ns
t _{d(off)}	turn-off delay time	1	-	17	-	ns
t _f	fall time	_	-	4	-	ns
Source-dra	in diode			-	1	
V _{SD}	source-drain voltage	$I_S = 0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V

20 V, N-channel Trench MOSFET

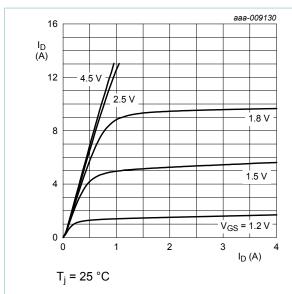


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

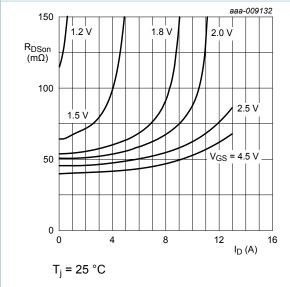


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

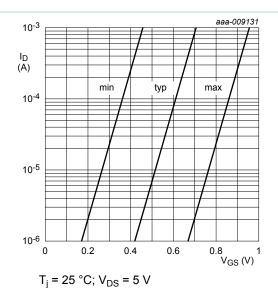


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

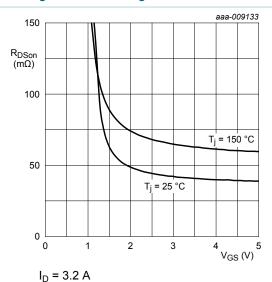


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, N-channel Trench MOSFET

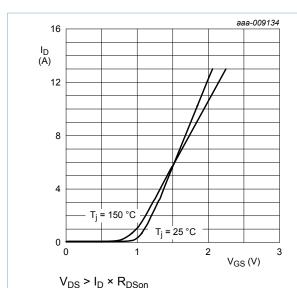


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

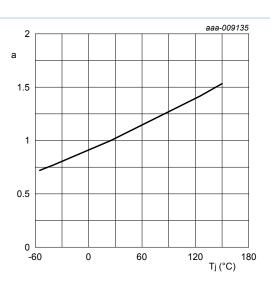


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

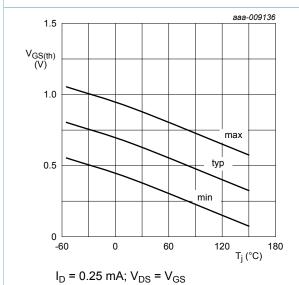
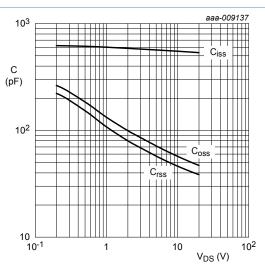


Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

8 / 15

20 V, N-channel Trench MOSFET

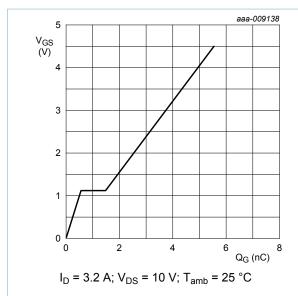


Fig. 15. Gate-source voltage as a function of gate charge; typical values

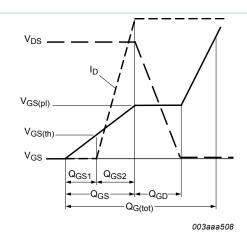


Fig. 16. MOSFET transistor: Gate charge waveform definitions

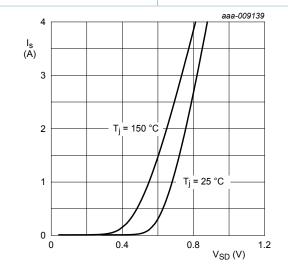
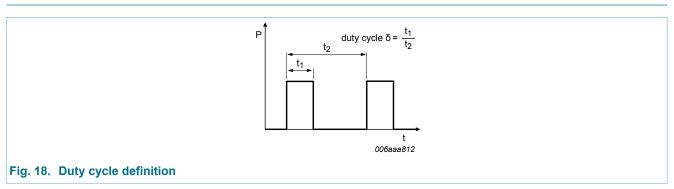


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

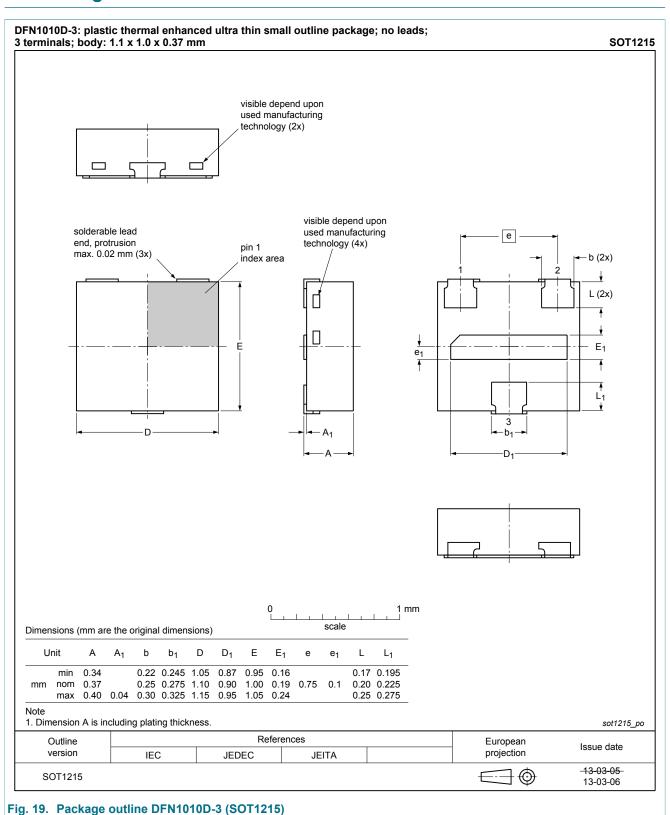


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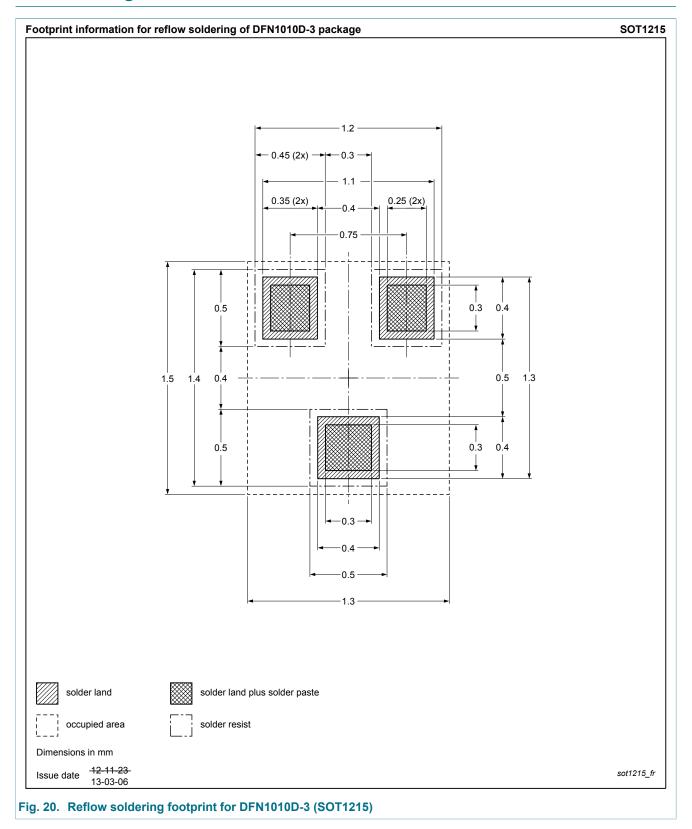
20 V, N-channel Trench MOSFET

12. Package outline



20 V, N-channel Trench MOSFET

13. Soldering



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20 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB43UNE v.1	20130919	Product data sheet	-	-

20 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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20 V, N-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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